

SILICON PNP TRIPLE DIFFUSED TYPE (PCT PROCESS)

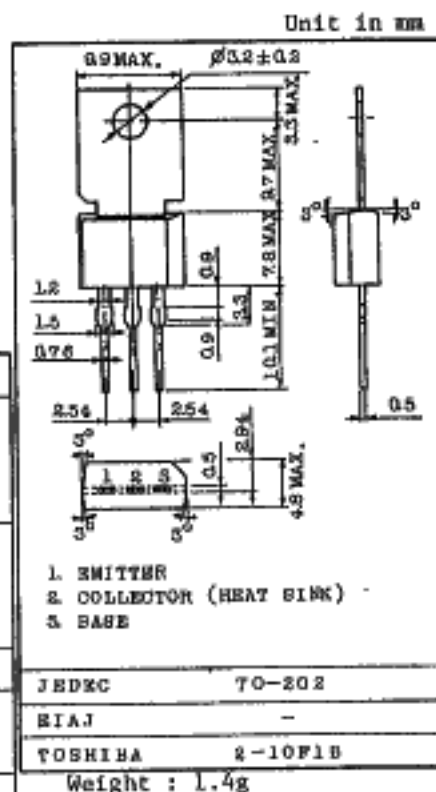
**TBF870**  
**TBF872**

HIGH VOLTAGE SWITCHING AND AMPLIFIER APPLICATIONS.  
COLOR TV CHROMA OUTPUT APPLICATIONS.

. NPN Complements are TBF869 and TBF871.

MAXIMUM RATINGS ( $T_B=25^{\circ}\text{C}$ )

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage	TBF870	$V_{CBO}$	-250	V
	TBF872		-300	
Collector-Emitter Voltage	TBF870	$V_{CEO}$	-250	V
	TBF872		-300	
Emitter-Base Voltage		$V_{EBO}$	-5	V
Collector Current	DC	$I_C$	-50	mA
	Peak	$I_{CP}$	-100	
Total Power Dissipation		$P_{tot}$	1.6	W
			5.0 ( $T_c=25^{\circ}\text{C}$ )	
Base Current		$I_B$	-20	mA
Junction Temperature		$T_j$	150	$^{\circ}\text{C}$
Storage Temperature Range		$T_{stg}$	-65 ~ 150	$^{\circ}\text{C}$
Solder Temperature, 1.5mm from Case for 10 Seconds		-	350	$^{\circ}\text{C}$



#### THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Thermal Resistance (Junction-Ambient)	$R_{\theta JA}$	78.3	$^{\circ}\text{C/W}$
Thermal Resistance (Junction-Case)	$R_{\theta JC}$	25	$^{\circ}\text{C/W}$

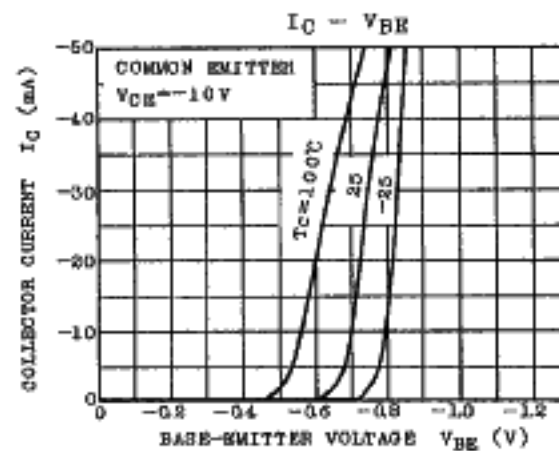
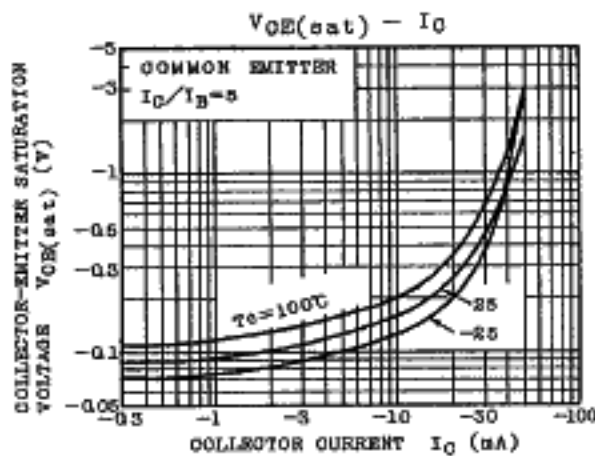
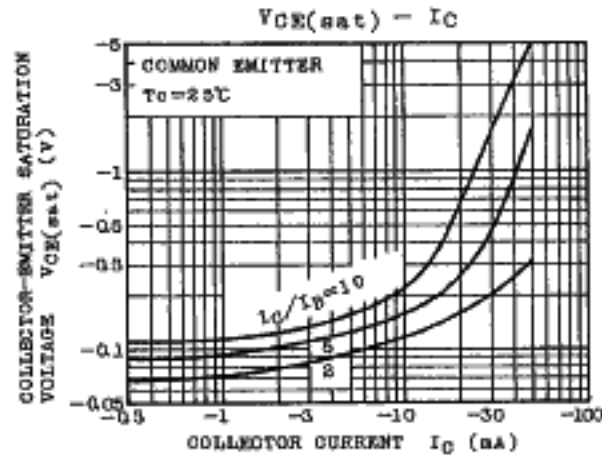
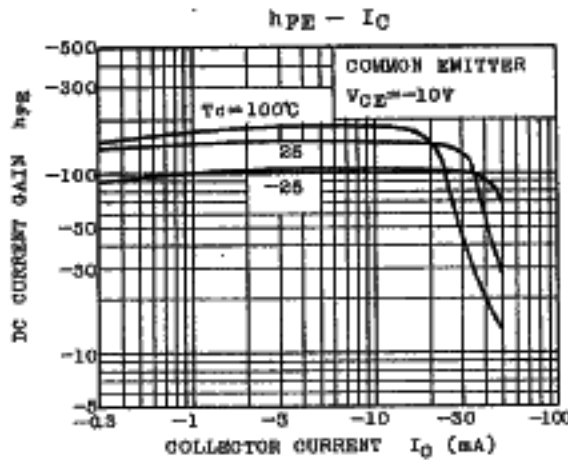
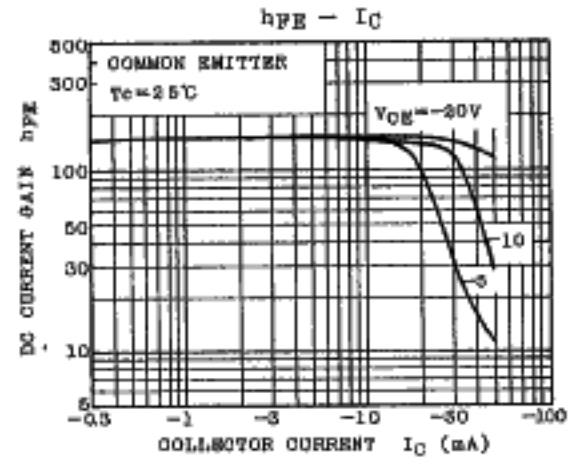
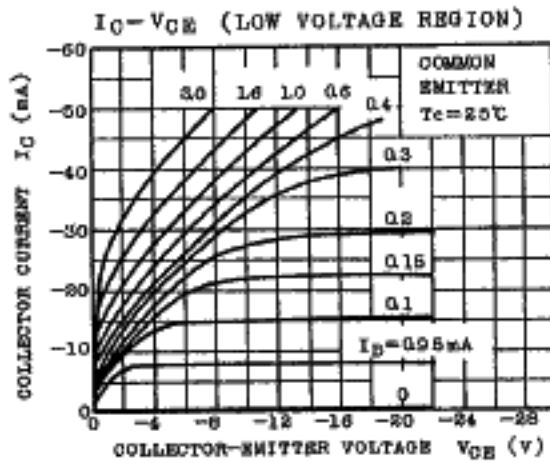
TOSHIBA CORPORATION

# TBF870 • TBF872

ELECTRICAL CHARACTERISTICS ( $T_a=25^{\circ}\text{C}$  Unless otherwise specified)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	TBF870	$I_{CBO}$	$V_{CB}=-200\text{V}, I_E=0$	-	-	-0.1	$\mu\text{A}$
	TBF872	$I_{CER}$	$V_{CE}=-250\text{V}, R_{BE}=2.7\text{k}\Omega$	-	-	-0.05	
Emitter Cut-off Current		$I_{EBO}$	$V_{EB}=-5\text{V}, I_C=0$	-	-	-10	$\mu\text{A}$
Collector-Emitter Breakdown Voltage	TBF870	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-250	-	-	V
	TBF872	$V_{(BR)CER}$	$I_C=-1\text{mA}, R_{BE}=2.7\text{k}\Omega$	-300	-	-	
High Temperature Collector Cut-off Current		$I_{CER}$	$V_{CE}=-200\text{V}, R_{BE}=2.7\text{k}\Omega$ $T_j=150^{\circ}\text{C}$	-	-	-10	$\mu\text{A}$
DC Current Gain		$h_{FE}$	$V_{CE}=-20\text{V}, I_C=-25\text{mA}$	50	-	-	
Collector-Emitter RF Saturation Voltage		$V_{CE(sat)RF}$	$I_C=-25\text{mA}, T_j=150^{\circ}\text{C}$	-	-20	-	V
Base-Emitter Voltage		$V_{BE}$	$V_{CE}=-20\text{V}, I_C=-25\text{mA}$	-	-0.75	-	V
Transition Frequency		$f_T$	$V_{CE}=-10\text{V}, I_C=-10\text{mA}$	60	80	-	MHz
Reverse Transfer Capacitance		$C_{re}$	$V_{CB}=-30\text{V}, I_E=0, f=1\text{MHz}$	-	1.7	2.0	pF

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